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IXYS Corporation
VVZB120-16IOX

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IXYS **VVZB120-16ioX**

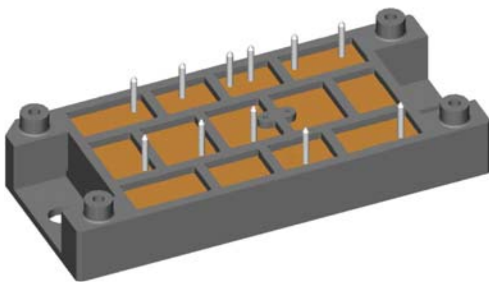
Thyristor Module

3~ Rectifier		Brake Chopper	
V_{RRM} =	1600 V	V_{CES} =	1200 V
I_{DAV} =	180 A	I_{C25} =	155 A
I_{FSM} =	700 A	$V_{CE(sat)}$ =	2.05 V

3~ Rectifier Bridge, half-controlled (high-side) + Brake Unit

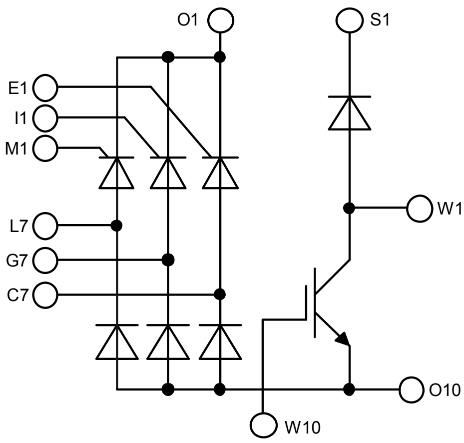
Part number

VVZB120-16ioX



Backside: isolated

E72873



Features / Advantages:

- Package with DCB ceramic base plate
- Improved temperature and power cycling
- Planar passivated chips
- Very low forward voltage drop
- Very low leakage current

Applications:

- 3~ Rectifier with brake unit for drive inverters

Package: V2-Pack

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Height: 17 mm
- Base plate: DCB ceramic
- Reduced weight
- Advanced power cycling

Rectifier

Symbol	Definition	Conditions		min.	typ.	max.	Unit
$V_{RSM/DSM}$	*max. non-repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1700	V
$V_{RRM/DRM}$	*max. repetitive reverse/forward blocking voltage*		T_{VJ} = 25°C			1600	V
$I_{R/D}$	*reverse current, drain current*	$V_{R/D}$ = 1600 V	T_{VJ} = 25°C			50	µA
		$V_{R/D}$ = 1600 V	T_{VJ} = 150°C			20	mA
V_T	*forward voltage drop*	I_T = 60 A	T_{VJ} = 25°C			1.27	V
		I_T = 180 A				1.90	V
		I_T = 60 A	T_{VJ} = 125°C			1.25	V
		I_T = 180 A				2.04	V
I_{DAV}	*bridge output current*	T_C = 85°C; rectangular d = ⅓	T_{VJ} = 150°C			180	A
V_{T0}	*threshold voltage*	*for power loss calculation only*	T_{VJ} = 150°C			0.83	V
r_T	*slope resistance*	*for power loss calculation only*				6.9	mΩ
R_{thJC}	*thermal resistance junction to case*					0.5	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.10		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			250	W
I_{TSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			700	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			755	A
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			595	A
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			645	A
I^2t	*value for fusing*	t = 10 ms; (50 Hz), sine	T_{VJ} = 45°C			2.45	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			2.37	kA²s
		t = 10 ms; (50 Hz), sine	T_{VJ} = 150°C			1.77	kA²s
		t = 8,3 ms; (60 Hz), sine	V_R = 0 V			1.73	kA²s
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		54		pF
P_{GM}	*max. gate power dissipation*	t_P = 30 µs	T_C = 150°C			10	W
		t_P = 300 µs				5	W
P_{GAV}	*average gate power dissipation*					0.5	W
$(di/dt)_{cr}$	*critical rate of rise of current*	T_{VJ} = 150°C; f = 50 Hz; t_P = 200 µs; di_G/dt = 0.45 A/µs;	repetitive, I_T = 180 A			150	A/µs
		I_G = 0.45A; V_D = ⅔ V_{DRM}	non-repet., I_T = 60 A			500	A/µs
$(dv/dt)_{cr}$	*critical rate of rise of voltage*	V_D = ⅔ V_{DRM}; R_{GK} = ∞; method 1 (linear voltage rise)	T_{VJ} = 150°C			1000	V/µs
V_{GT}	*gate trigger voltage*	V_D = 6 V	T_{VJ} = 25°C			1.5	V
			T_{VJ} = -40°C			1.6	V
I_{GT}	*gate trigger current*	V_D = 6 V	T_{VJ} = 25°C			95	mA
			T_{VJ} = -40°C			200	mA
V_{GD}	*gate non-trigger voltage*	V_D = ⅔ V_{DRM}	T_{VJ} = 150°C			0.2	V
I_{GD}	*gate non-trigger current*					10	mA
I_L	*latching current*	t_p = 10 µs; I_G = 0.45A; di_G/dt = 0.45 A/µs	T_{VJ} = 25°C			450	mA
I_H	*holding current*	V_D = 6 V R_{GK} = ∞	T_{VJ} = 25°C			200	mA
t_{gd}	*gate controlled delay time*	V_D = ½ V_{DRM}; I_G = 0.45A; di_G/dt = 0.45 A/µs	T_{VJ} = 25°C			2	µs
t_q	*turn-off time*	V_R = 100 V; I_T = 60 A; V_D = ⅔ V_{DRM}; di/dt = 10 A/µs; dv/dt = 20 V/µs; t_p = 200 µs	T_{VJ} = 150°C		150		µs

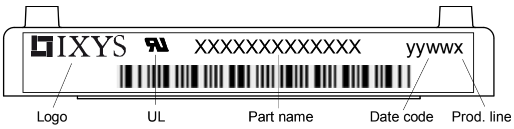
Brake IGBT

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{CES}	*collector emitter voltage*		T_{VJ} = 25°C			1200	V
V_{GES}	*max. DC gate voltage*					±20	V
V_{GEM}	*max. transient gate emitter voltage*					±30	V
I_{C25}	*collector current*		T_C = 25°C			155	A
I_{C80}			T_C = 80°C			108	A
P_{tot}	*total power dissipation*		T_C = 25°C			500	W
$V_{CE(sat)}$	*collector emitter saturation voltage*	I_C = 100 A; V_{GE} = 15 V	T_{VJ} = 25°C		2.05	2.35	V
			T_{VJ} = 125°C		2.45		V
$V_{GE(th)}$	*gate emitter threshold voltage*	I_C = 4 mA; V_{GE} = V_{CE}	T_{VJ} = 25°C	5.4	5.9	6.5	V
I_{CES}	*collector emitter leakage current*	V_{CE} = V_{CES}; V_{GE} = 0 V	T_{VJ} = 25°C			0.1	mA
			T_{VJ} = 125°C		0.1		mA
I_{GES}	*gate emitter leakage current*	V_{GE} = ±20 V				500	nA
$Q_{G(on)}$	*total gate charge*	V_{CE} = 600 V; V_{GE} = 15 V; I_C = 100 A			295		nC
$t_{d(on)}$	*turn-on delay time*	inductive load V_{CE} = 600 V; I_C = 100 A V_{GE} = ±15 V; R_G = 6.8 Ω	T_{VJ} = 125°C		70		ns
t_r	*current rise time*				40		ns
$t_{d(off)}$	*turn-off delay time*				250		ns
t_f	*current fall time*				100		ns
E_{on}	*turn-on energy per pulse*				8.5		mJ
E_{off}	*turn-off energy per pulse*				11.5		mJ
RBSOA	*reverse bias safe operating area*	V_{GE} = ±15 V; R_G = 6.8 Ω	T_{VJ} = 125°C				
I_{CM}		V_{CEK} = 1200 V				300	A
SCSOA	*short circuit safe operating area*						
t_{SC}	*short circuit duration*	V_{CE} = 720 V; V_{GE} = ±15 V	T_{VJ} = 125°C			10	µs
I_{SC}	*short circuit current*	R_G = 6.8 Ω; non-repetitive			400		A
R_{thJC}	*thermal resistance junction to case*					0.25	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.10		K/W

Brake Diode

Symbol	Definition	Conditions		min.	typ.	max.	Unit
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25°C			1200	V
I_{F25}	*forward current*		T_C = 25°C			48	A
I_{F80}			T_C = 80°C			32	A
V_F	*forward voltage*	I_F = 30 A	T_{VJ} = 25°C			2.75	V
			T_{VJ} = 125°C		1.80		V
I_R	*reverse current*	V_R = V_{RRM}	T_{VJ} = 25°C			0.25	mA
			T_{VJ} = 125°C			1	mA
Q_{rr}	*reverse recovery charge*	V_R = 600 V $-di_F/dt$ = 400 A/µs I_F = 30 A	T_{VJ} = 125°C		1.8		µC
I_{RM}	*max. reverse recovery current*				23		A
t_{rr}	*reverse recovery time*				150		ns
R_{thJC}	*thermal resistance junction to case*					0.9	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.3		K/W

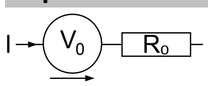
Package V2-Pack				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per terminal				100	A
T_{stg}	*storage temperature*			-40		125	°C
T_{VJ}	*virtual junction temperature*			-40		150	°C
Weight					76		g
M_D	*mounting torque*			2		2.5	Nm
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	6.0			mm
$d_{Spb/Apb}$			*terminal to backside*	12.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V



Ordering	Part Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	VVZB120-16ioX	VVZB120-16ioX	Box	6	511152

Equivalent Circuits for Simulation

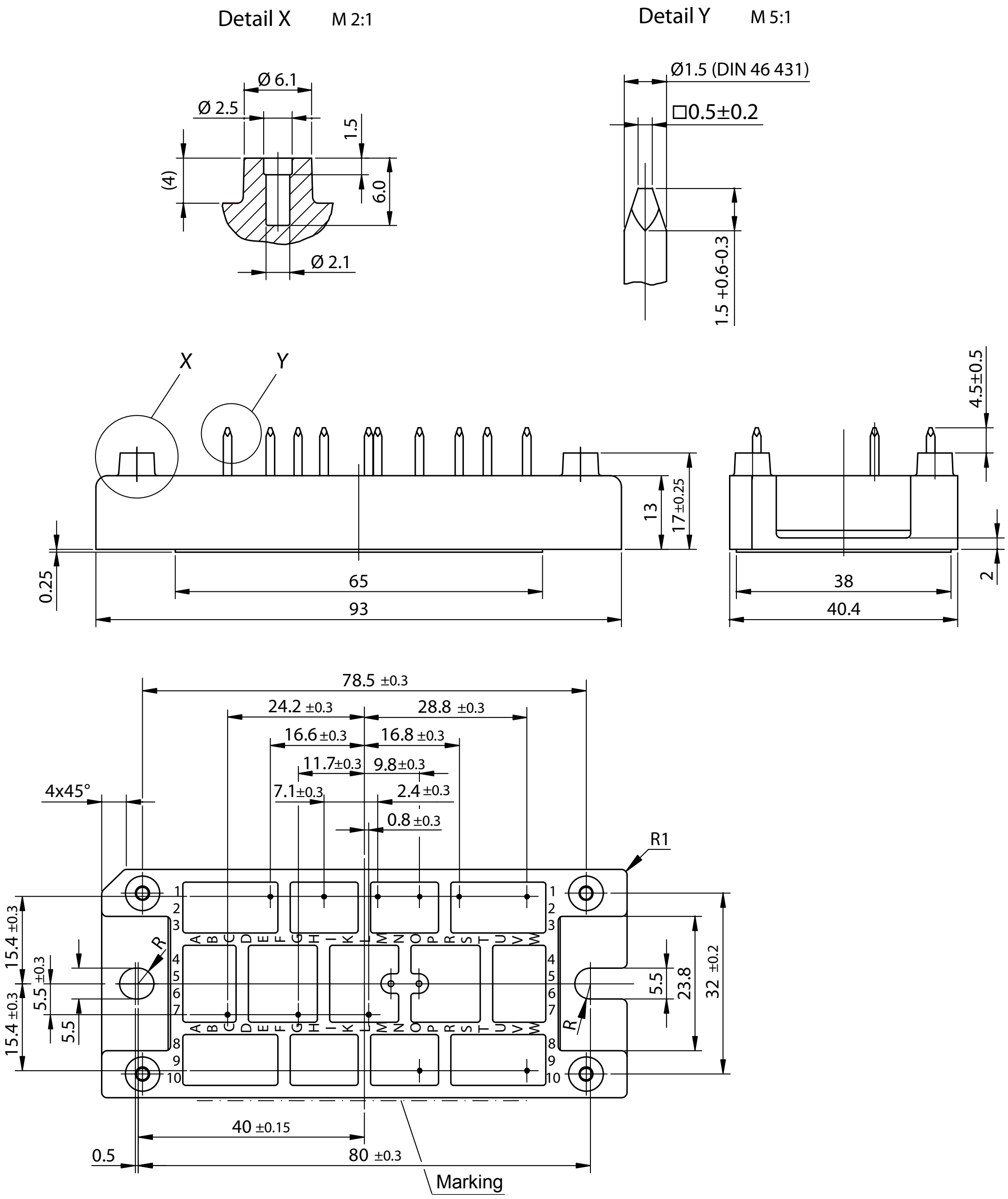
** on die level* T_{VJ} = 150 °C

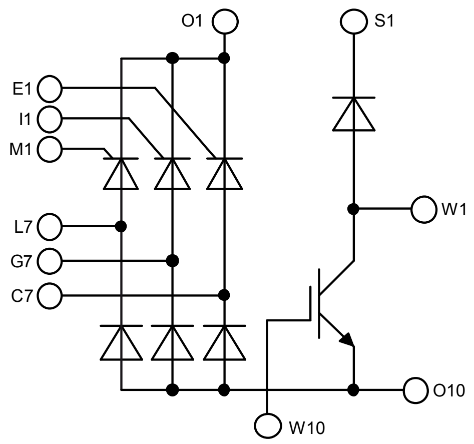


		Thyristor	Brake IGBT	Brake Diode	
$V_{0\,max}$	*threshold voltage*	0.83	1.1	1.31	V
$R_{0\,max}$	*slope resistance **	3.7	13.8	8	mΩ

IXYS **VVZB120-16ioX**

Outlines V2-Pack





Thyristor

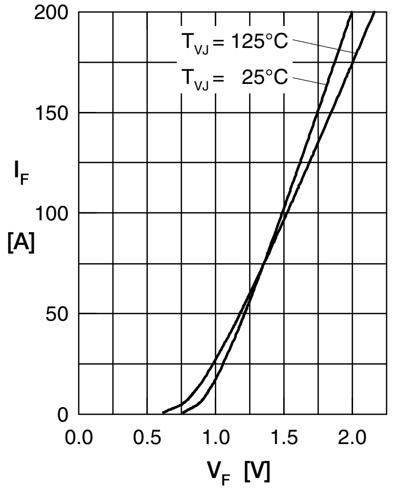


Fig. 1 Forward current vs. voltage drop per thyristor

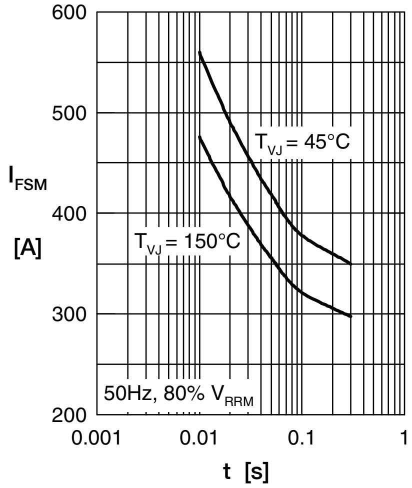


Fig. 2 Surge overload current vs. time per thyristor

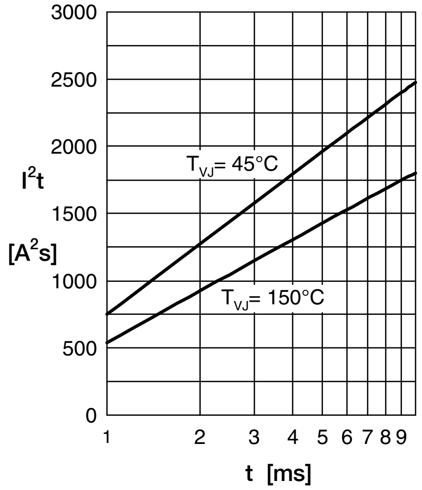


Fig. 3 I^2t vs. time per thyristor

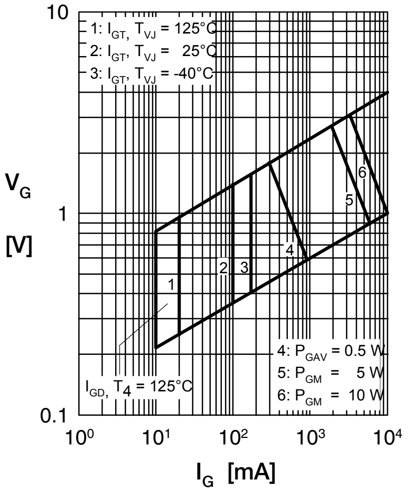


Fig. 4 Gate trigger characteristics

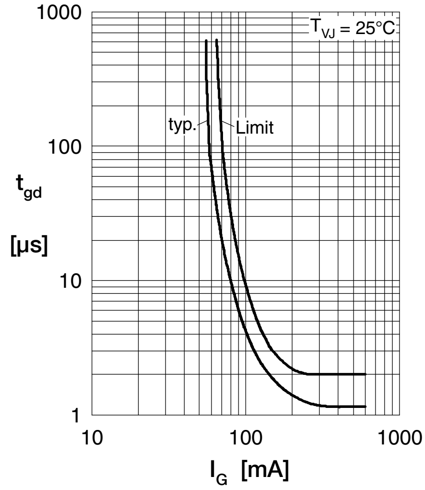


Fig. 5 Gate trigger delay time

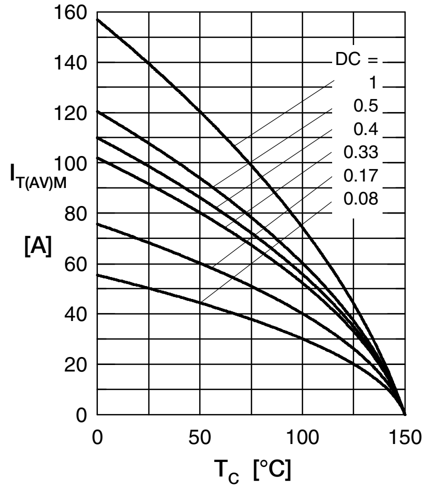


Fig. 5 Max. forward current vs. case temperature per thyristor

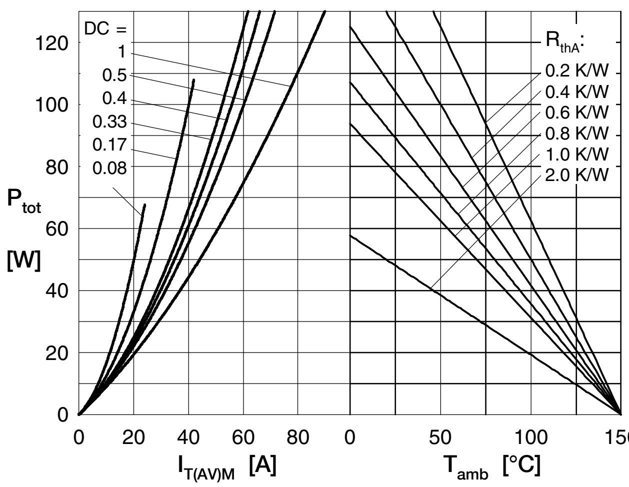
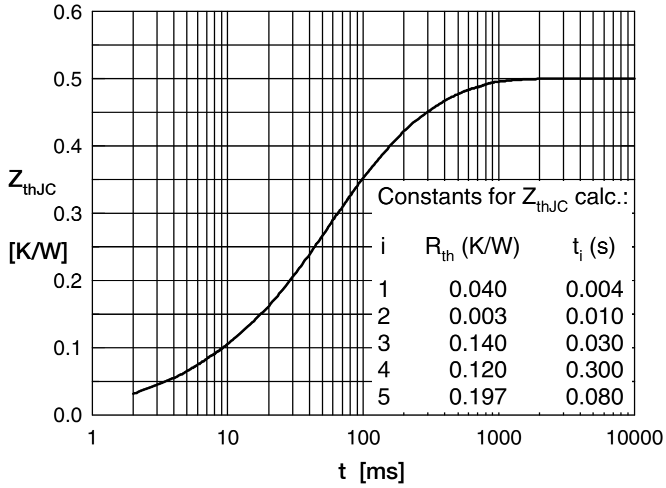


Fig. 4 Power dissipation vs. forward current and ambient temperature per thyristor



Constants for Z_{thJC} calc.:

i	R_{th} (K/W)	t_i (s)
1	0.040	0.004
2	0.003	0.010
3	0.140	0.030
4	0.120	0.300
5	0.197	0.080

Fig. 6 Transient thermal impedance junction to case vs. time per thyristor

Brake IGBT

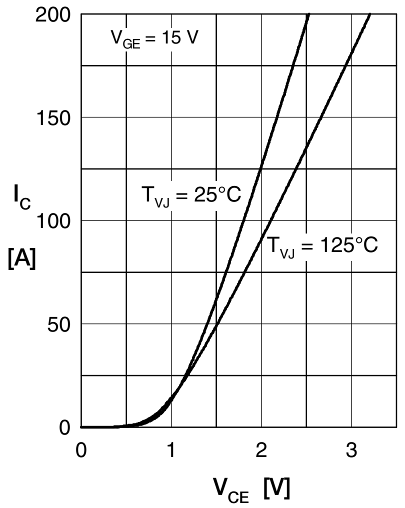


Fig. 1 Typ. output characteristics

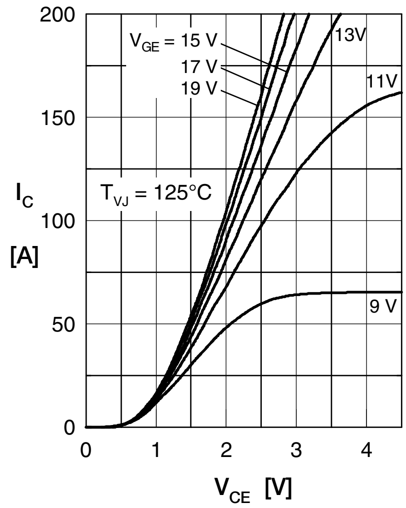


Fig. 2 Typ. output characteristics

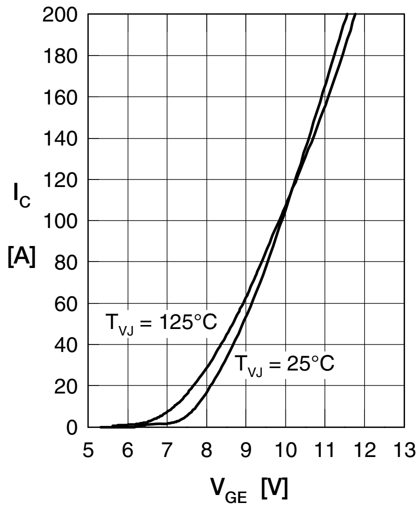


Fig. 3 Typ. tranfer characteristics

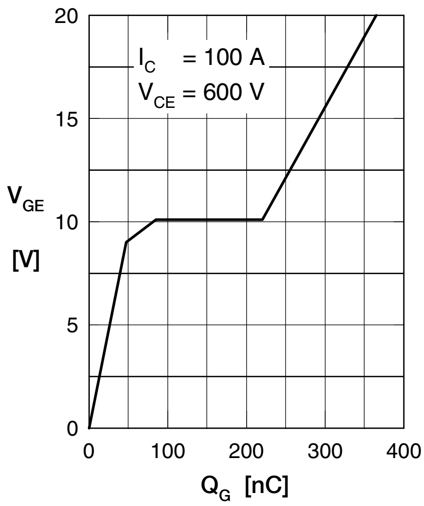


Fig. 4 Typ. turn-on gate charge

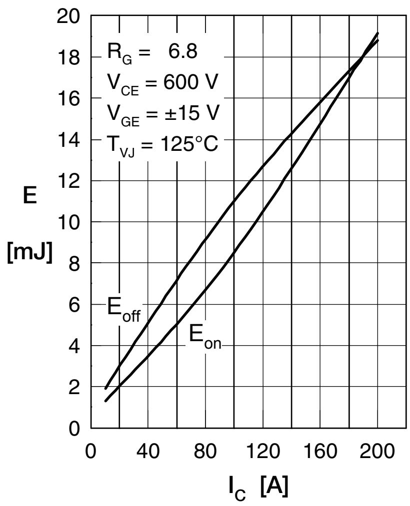


Fig. 5 Typ. switching energy versus collector current

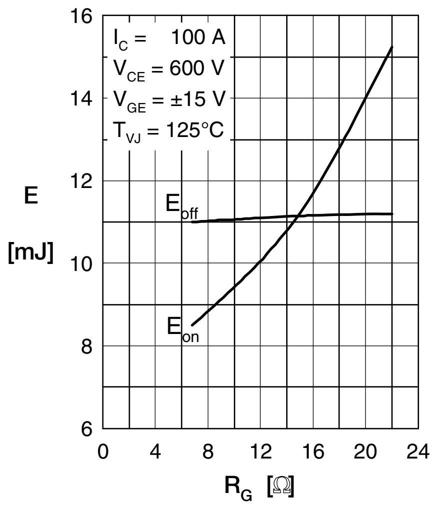


Fig. 6 Typ. switching energy versus gate resistance

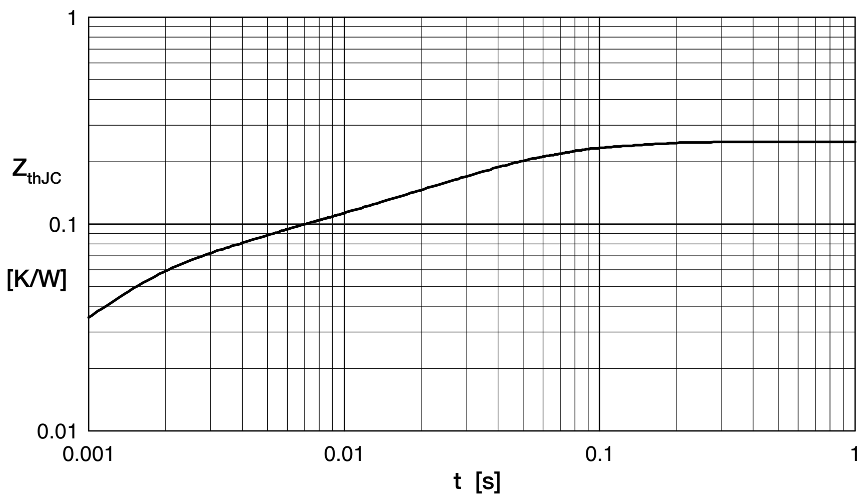


Fig. 7 Typ. transient thermal impedance junction to case

Brake Diode

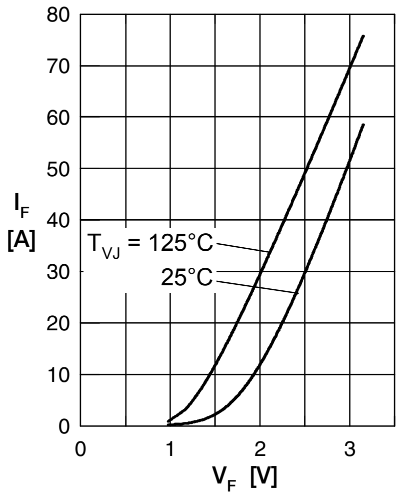


Fig. 1 Forward current I_F vs. V_F

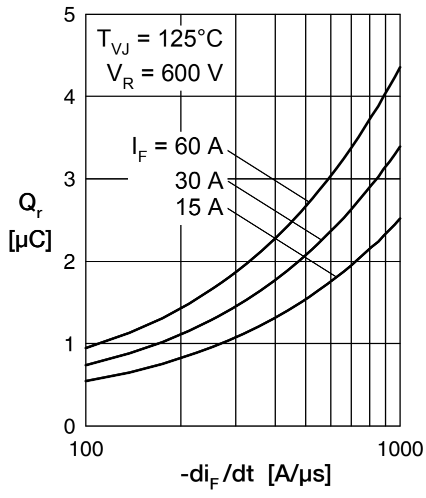


Fig. 2 Typ. reverse recovery charge Q_r versus $-di_F/dt$

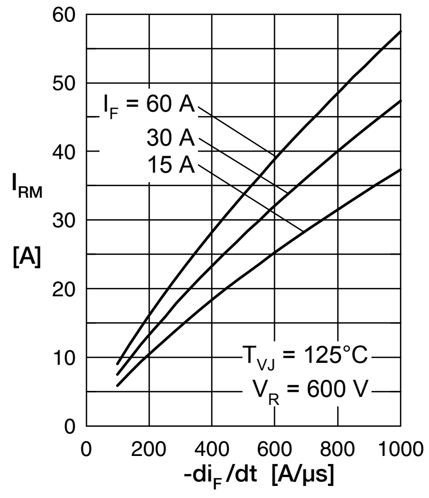


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

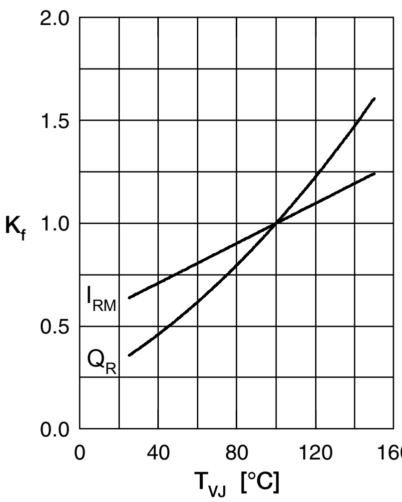


Fig. 4 Dynamic parameters Q_r, I_{RM} versus T_{VJ}

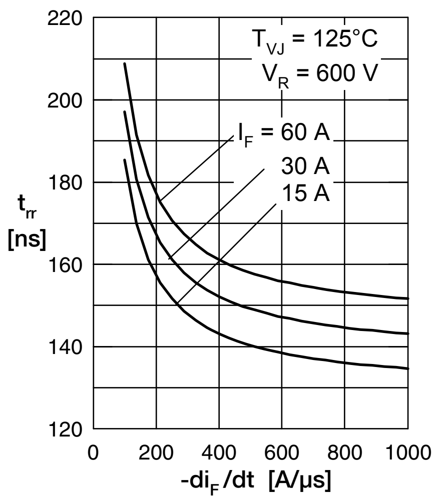


Fig. 5 Typ. recovery time t_{rr} vs. $-di_F/dt$

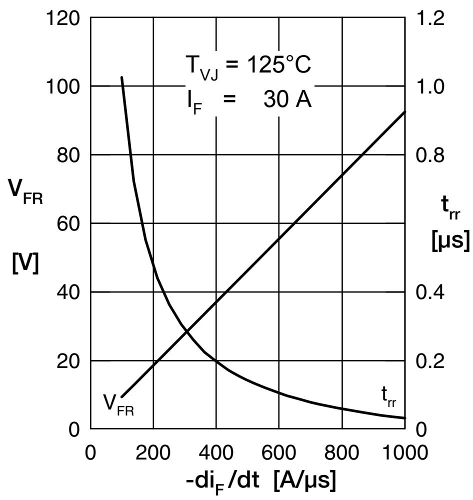


Fig. 6 Typ. peak forward voltage V_{FR} and t_{fr} versus di_F/dt

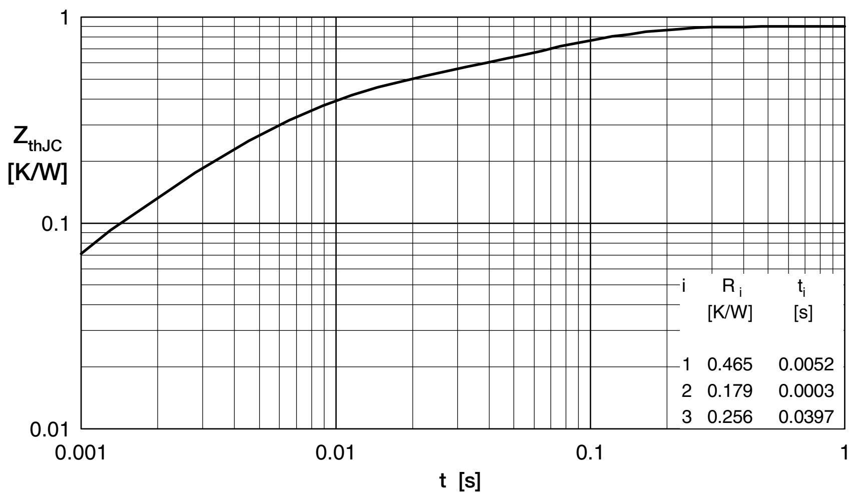


Fig. 7 Transient thermal impedance junction to case